Elektronische Bauelemente

SSPR32P03-C

-32A, -30V, $R_{DS(ON)}$ 27mΩ

P-Channel Enhancement Mode Power MOSFET

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

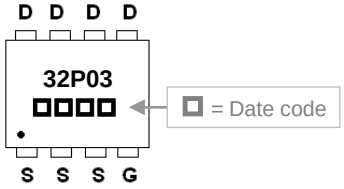
DESCRIPTION

The SSPR32P03-C provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness. The SPR-8PP package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

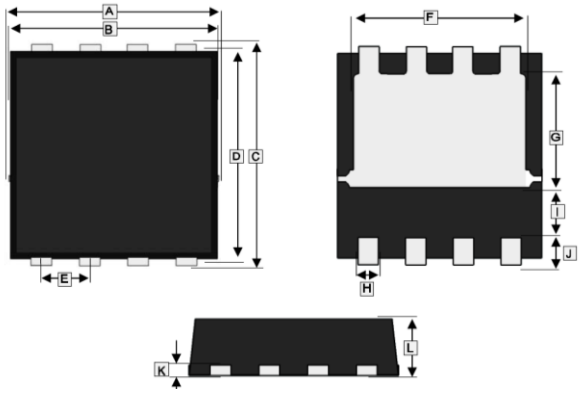
FEATURES

- Lower Gate Charge
- Simple Drive Requirement
- Fast Switching Characteristic

MARKING



SPR-8PP



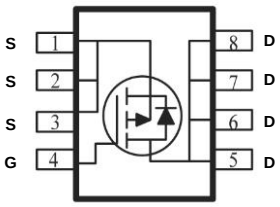
REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	3.00	3.40	G	1.35	1.98
B	3.00	3.25	H	0.24	0.35
C	3.20	3.45	I	0.35 TYP.	
D	3.00	3.20	J	0.60 TYP.	
E	0.65 BSC.		K	0.10	0.25
F	2.39	2.60	L	0.70	0.90

PACKAGE INFORMATION

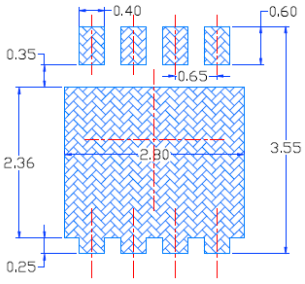
Package	MPQ	Leader Size
SPR-8PP	3K	13 inch

ORDER INFORMATION

Part Number	Type
SSPR32P03-C	Lead (Pb)-free and Halogen-free



Mounting Pad Layout



*Dimensions in millimeters

ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current [1] @V_{GS}=10V	T_C=25°C	I_D	-32	A
	T_C=100°C		-20	
	T_A=25°C		-7.7	
	T_A=70°C		-6.2	
Pulsed Drain Current [2]		I_{DM}	-65	A
Single Pulse Avalanche Energy [3]		E_{AS}	72.2	mJ
Avalanche Current		I_{AS}	-38	A
Power Dissipation [4]	T_C=25°C	P_D	29	W
	T_A=25°C		1.67	
Operating Junction & Storage Temperature		T_J, T_{STG}	-55~150	°C
Thermal Resistance Rating				
Thermal Resistance Junction-Ambient [1]		$R_{\theta JA}$	75	°C/W
Thermal Resistance Junction-Ambient [1] (t≤10s)			30	
Thermal Resistance Junction-Case [1]		$R_{\theta JC}$	4.32	

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage		BV_{DSS}	-30	-	-	V	V_{GS}=0, I_D= -250μA
Gate-Threshold Voltage		$V_{GS(th)}$	-1	-	-2.5	V	V_{DS}=V_{GS}, I_D= -250μA
Forward Transconductance		g_{fs}	-	19	-	S	V_{DS}= -5V, I_D= -15A
Gate-Source Leakage Current		I_{GSS}	-	-	±100	nA	V_{GS}= ±25V, V_{DS}=0
Drain-Source Leakage Current	T_J=25°C	I_{DSS}	-	-	-1	μA	V_{DS}= -24V, V_{GS}=0
	T_J=55°C		-	-	-5		
Static Drain-Source On-Resistance [2]		$R_{DS(ON)}$	-	-	27	mΩ	V_{GS}= -10V, I_D= -15A
			-	-	32		V_{GS}= -4.5V, I_D= -10A
Gate Resistance		R_g	-	13	-	Ω	V_{DS}=0V, V_{GS}=0V, f=1MHz
Total Gate Charge		Q_g	-	12.5	-	nC	I_D= -15A V_{DS}= -15V V_{GS}= -4.5V
Gate-Source Charge		Q_{gs}	-	5.4	-		
Gate-Drain Change		Q_{gd}	-	5	-		
Turn-on Delay Time		$T_{d(on)}$	-	4.4	-	nS	V_{DD}= -15V I_D= -15A V_{GS}= -10V R_G=3.3Ω
Rise Time		T_r	-	11.2	-		
Turn-off Delay Time		$T_{d(off)}$	-	34	-		
Fall Time		T_f	-	18	-		
Input Capacitance		C_{iss}	-	1275	-	pF	V_{GS}=0 V_{DS}= -15V f=1MHz
Output Capacitance		C_{oss}	-	194	-		
Reverse Transfer Capacitance		C_{rss}	-	158	-		
Source-Drain Diode							
Diode Forward Voltage [2]		V_{SD}	-	-	-1.2	V	I_S= -1A, V_{GS}=0, T_J=25°C
Continuous Source Current [1,5]		I_S	-	-	-32	A	V_D=V_G=0, Force Current
Pulsed Source Current [2,5]		I_{SM}	-	-	-65	A	
Reverse Recovery Time		T_{rr}	-	12.4	-	nS	I_F= -15A, dI/dt=100A/μs, T_J=25°C
Reverse Recovery Charge		Q_{rr}	-	5	-	nC	

Notes:

1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2oz copper.
2. The data tested by pulsed, pulse width≦300us, duty cycle≦2%.
3. The E_{AS} data shows Max. rating. The test condition is V_{DD}= -25V, V_{GS}= -10V, L=0.1mH, I_{AS}= -38A.
4. The power dissipation is limited by 150°C junction temperature.
5. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

CHARACTERISTIC CURVES

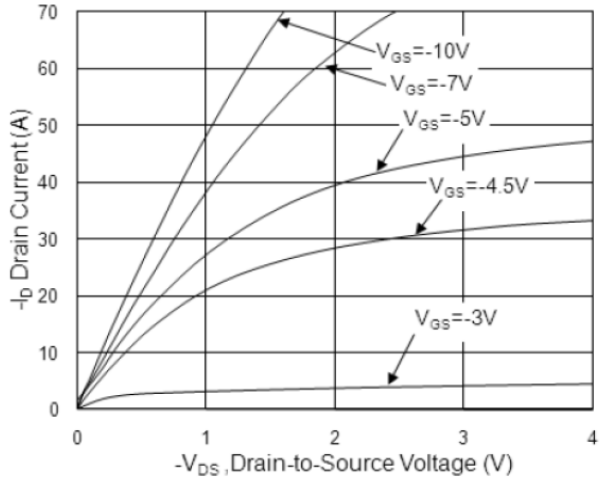


Fig.1 Typical Output Characteristics

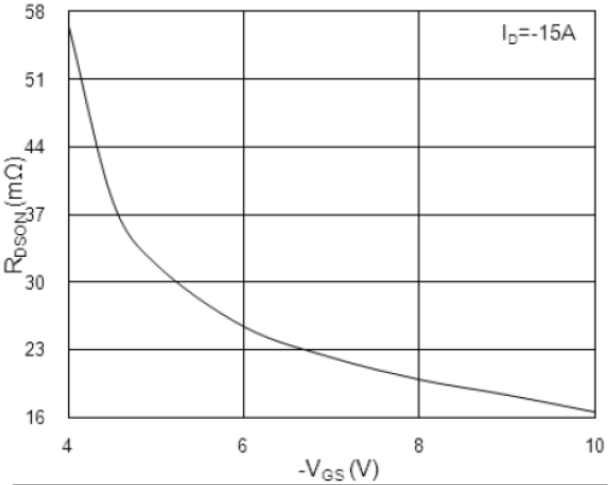


Fig.2 On-Resistance v.s Gate-Source

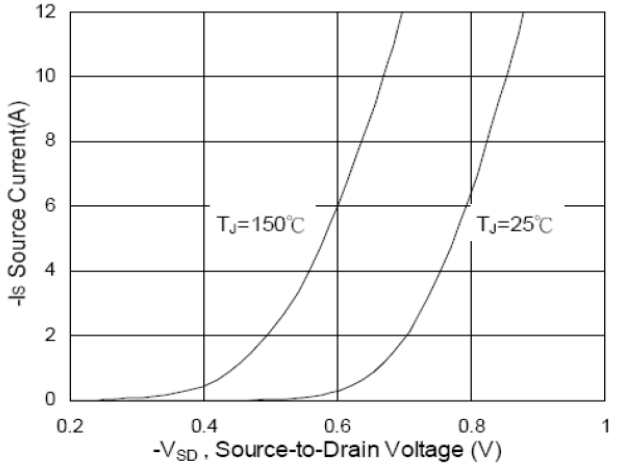


Fig.3 Forward Characteristics of Reverse

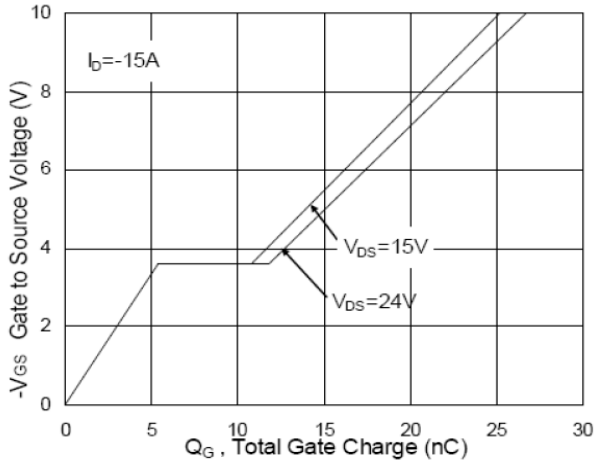


Fig.4 Gate-Charge Characteristics

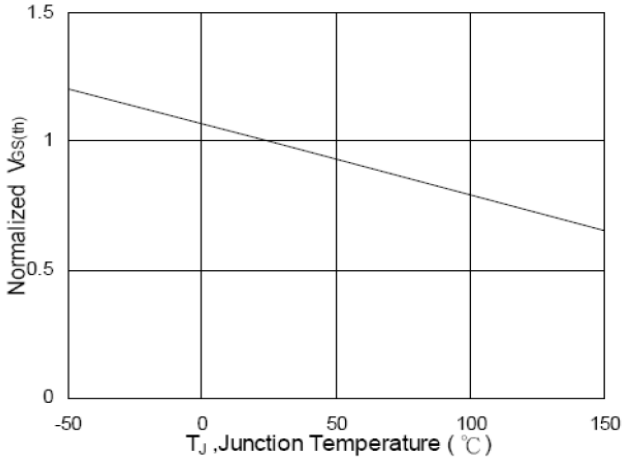


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

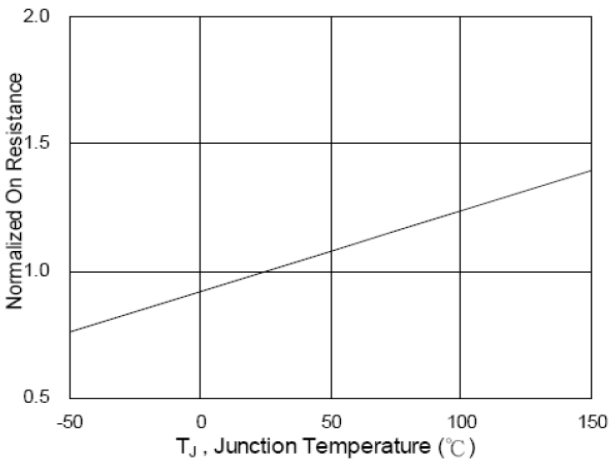


Fig.6 Normalized R_{DSON} v.s T_J

CHARACTERISTIC CURVES

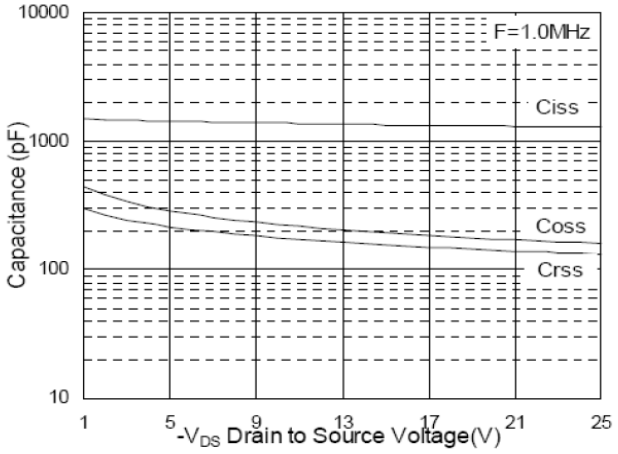


Fig.7 Capacitance

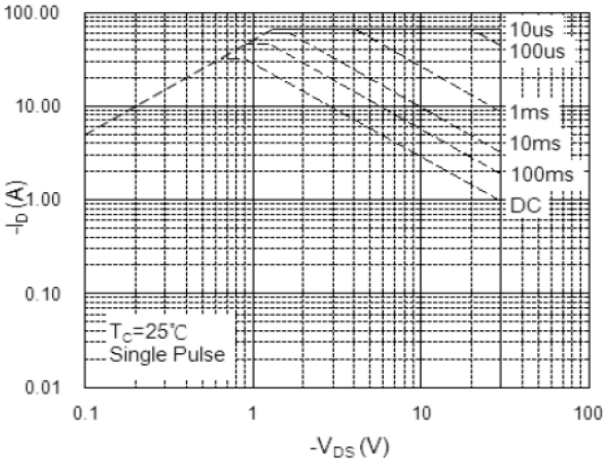


Fig.8 Safe Operating Area

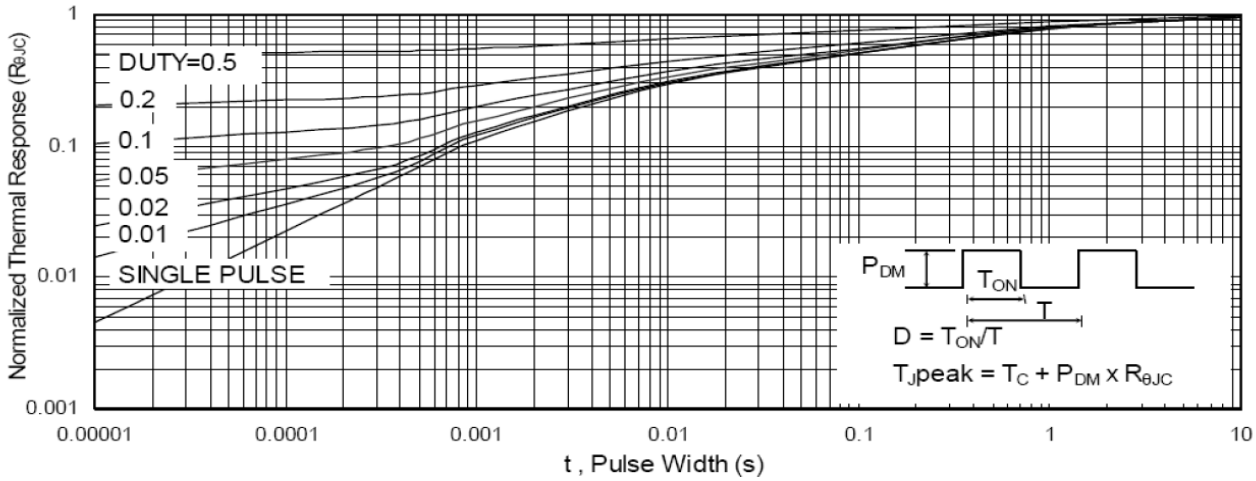


Fig.9 Normalized Maximum Transient Thermal Impedance

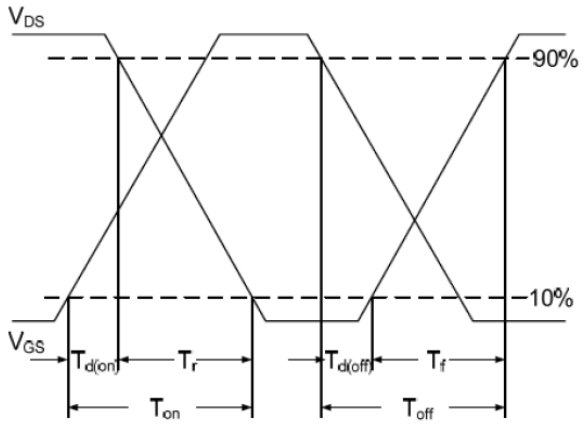


Fig.10 Switching Time Waveform

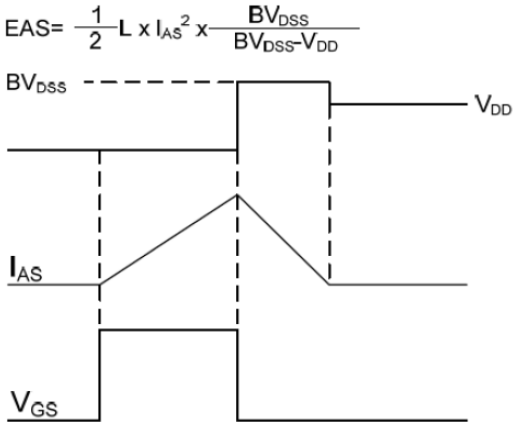


Fig.11 Unclamped Inductive Switching Wave